



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

DMBTA92

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

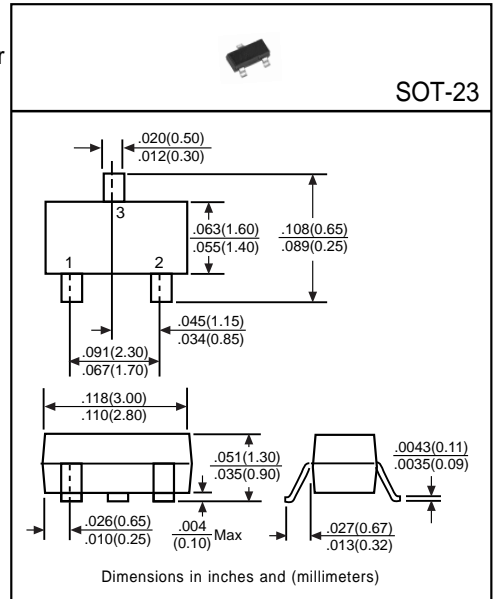
Designed for application as a video output to drive color CRT, or as a dialer circuit in electronics telephone.

Pinning

- 1 = Base
- 2 = Emitter
- 3 = Collector

Absolute Maximum Ratings (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-300	V
Collector-Emitter Voltage	V _{CE0}	-300	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-500	mA
Total Power Dissipation	P _D	225	mW
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CB0}	-300	-	-	V	I _C =-100μA
Collector-Emitter Breakdown Voltage	BV _{CE0}	-300	-	-	V	I _C =-1mA
Emitter-Base Breakdown Voltage	BV _{EB0}	-5	-	-	V	I _E =-10μA
Collector Cutoff Current	I _{CBO}	-	-	-250	nA	V _{CB} =-200V
Emitter Cutoff Current	I _{EBO}	-	-	-100	nA	V _{EB} =-3V
Collector-Emitter Saturation Voltage ⁽¹⁾	V _{CE(sat)}	-	-	-0.5	V	I _C =-20mA, I _B =-2mA
Base-Emitter Saturation Voltage ⁽¹⁾	V _{BE(sat)}	-	-	-0.9	V	I _C =-20mA, I _B =-2mA
DC Current Gain ⁽¹⁾	hFE1	25	-	-	-	I _C =-1mA, V _{CE} =-10V
	hFE2	40	-	-	-	I _C =-10mA, V _{CE} =-10V
	hFE3	25	-	-	-	I _C =-30mA, V _{CE} =-10V
Transition Frequency	f _T	50	-	-	MHz	I _C =-10mA, V _{CE} =-20V, f=100MHz
Output Capacitance	C _{ob}	-	-	6	pF	V _{CB} =-20V, f=1MHz

(1) Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%